

PART NUMBER

EP610LI-15-ROCA

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

• Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.



EP610-910-1810

Classic EPLD Family

The Altera Classic[™] device family offers a solution to high-speed, low-power logic integration. Fabricated on advanced CMOS technology, Classic devices also have a Turbo-only version, which is described in the data sheet.

Classic devices support 100% TTL emulation and can easily integrate multiple PAL- and GAL-type devices with densities ranging from 300 to 900 usable gates. The Classic family provides pin-to-pin logic delays as low as 10 ns and counter frequencies as high as 100 MHz. Classic devices are available in a wide range of packages, including ceramic dual in-line package (CerDIP), plastic dual in-line package (PDIP), plastic J-lead chip carrier (PLCC), ceramic J-lead chip carrier JLCC), pin-grid array (PGA), and small-outline integrated circuit (SOIC) packages.

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FOR REFERENCE ONLY

General Description

The Altera Classic[™] device family offers a solution to high-speed, lowpower logic integration. Fabricated on advanced CMOS technology, Classic devices also have a Turbo-only version, which is described in this data sheet.

Classic devices support 100% TTL emulation and can easily integrate multiple PAL- and GAL-type devices with densities ranging from 300 to 900 usable gates. The Classic family provides pin-to-pin logic delays as low as 10 ns and counter frequencies as high as 100 MHz. Classic devices are available in a wide range of packages, including ceramic dual in-line package (CerDIP), plastic dual in-line package (PDIP), plastic J-lead chip carrier (PLCC), ceramic J-lead chip carrier (JLCC), pin-grid array (PGA), and small-outline integrated circuit (SOIC) packages.

EPROM-based Classic devices can reduce active power consumption without sacrificing performance. This reduced power consumption makes the Classic family well suited for a wide range of low-power applications.

Classic devices are 100% generically tested devices in windowed packages and can be erased with ultra-violet (UV) light, allowing design changes to be implemented quickly.

Classic devices use sum-of-products logic and a programmable register. The sum-of-products logic provides a programmable-AND/fixed-OR structure that can implement logic with up to eight product terms. The programmable register can be individually programmed for D, T, SR, or JK flipflop operation or can be bypassed for combinatorial operation. In addition, macrocell registers can be individually clocked either by a global clock or by any input or feedback path to the AND array. Altera's proprietary programmable I/O architecture allows the designer to program output and feedback paths for combinatorial or registered operation in both active-high and active-low modes. These features make it possible to implement a variety of logic functions simultaneously.

Classic devices are supported by Altera's MAX+PLUS II development system, a single, integrated package that offers schematic, text—including VHDL, Verilog HDL, and the Altera Hardware Description Language (AHDL)—and waveform design entry, compilation and logic synthesis, simulation and timing analysis, and device programming. The MAX+PLUS II software provides EDIF 2 0 0 and 3 0 0, LPM, VHDL, Verilog HDL, and other interfaces for additional design entry and simulation support from other industry-standard PC- and workstationbased EDA tools. The MAX+PLUS II software runs on Windows-based PCs, as well as Sun SPARCstation, HP 9000 Series 700/800, and IBM RISC System/6000 workstations. These devices also contain on-board logic test circuitry to allow verification of function and AC specifications during standard production flow.

Rochester Ordering Guide

*Most products can also be offered as RoHS compliant, designated by a –G suffix. Please contact factory for more information.

Rochester Part Number	Altera Part Number	Package	Temperature
EP600DI-25	EP600DI-25	CDIP-24	-40° to +85°C
EP600DI-25T	EP600DI-25T	CDIP-24	-40° to +85°C
EP600DI-30	EP600DI-30	CDIP-24	-40° to +85°C
EP600DI-35	EP600DI-35	CDIP-24	-40° to +85°C
EP600DI-45	EP600DI-45	CDIP-24	-40° to +85°C
EP600DM-25/B	EP600DM-25/B	CDIP-24	-55° to +125°C
EP600DM-25T/B	EP600DM-25T/B	CDIP-24	-55° to +125°C
EP600DM-30/B	EP600DM-30/B	CDIP-24	-55° to +125°C
EP600DM-35/B	EP600DM-35/B	CDIP-24	-55° to +125°C
EP600DM-45/B	EP600DM-45/B	CDIP-24	-55° to +125°C
EP600IDC-25	EP600IDC-25	CDIP-24	0° to +70°C
EP600IDC-30	EP600IDC-30	CDIP-24	0° to +70°C
EP600IDC-35	EP600IDC-35	CDIP-24	0° to +70°C
EP600IDC-45	EP600IDC-45	CDIP-24	0° to +70°C
EP600ILC-45	EP600ILC-45	LDCC-28, Plastic	0° to +70°C
EP600IPC-25	EP600IPC-25	PDIP-24	0° to +70°C
EP600IPC-30	EP600IPC-30	PDIP-24	0° to +70°C
EP600IPC-35	EP600IPC-35	PDIP-24	0° to +70°C
EP600IPC-45	EP600IPC-45	PDIP-24	0° to +70°C
EP600IPC-45	EP600IPC-45	PDIP-24	0° to +70°C
EP600IPC-45AB	EP600IPC-45AB	PDIP-24	0° to +70°C
EP610DC-25	EP610DC-25	CDIP-24	0° to +70°C
EP610DC-30	EP610DC-30	CDIP-24	0° to +70°C
EP610DC-35	EP610DC-35	CDIP-24	0° to +70°C
EP610DC-35AA	EP610DC-35AA	CDIP-24	0° to +70°C
EP610DC-45	EP610DC-45	CDIP-24	0° to +70°C
EP610DI-15	EP610DI-15	CDIP-24	-40° to +85°C
EP610DI-20	EP610DI-20	CDIP-24	-40° to +85°C
EP610DI-25	EP610DI-25	CDIP-24	-40° to +85°C
EP610DI-25T	EP610DI-25T	CDIP-24	-40° to +85°C
EP610DI-30	EP610DI-30	CDIP-24	-40° to +85°C
EP610DI-35	EP610DI-35	CDIP-24	-40° to +85°C
EP610DM-25	EP610DM-25	CDIP-24	-55° to +125°C
EP610DM-25T	EP610DM-25T	CDIP-24	-55° to +125°C
EP610DM-30	EP610DM-30	CDIP-24	-55° to +125°C
EP610DM-35	EP610DM-35	CDIP-24	-55° to +125°C
EP610DM-35/B	EP610DM-35/B	CDIP-24	-55° to +125°C
EP610DM-25/R	EP610DM-25/R	CDIP-24	-55° to +125°C
EP610DM-25T/R	EP610DM-25T/R	CDIP-24	-55° to +125°C
EP610DM-30/R	EP610DM-30/R	CDIP-24	-55° to +125°C
EP610DM-35/R	EP610DM-35/R	CDIP-24	-55° to +125°C
EP610LC-15	EP610LC-15	LDCC-28, Plastic	0° to +70°C
EP610LC-20	EP610LC-20	LDCC-28, Plastic	0° to +70°C
EP610LC-20T	EP610LC-20T	LDCC-28, Plastic	0° to +70°C
EP610LC-25	EP610LC-25	LDCC-28, Plastic	0° to +70°C
EP610LC-35	EP610LC-35	LDCC-28, Plastic	0° to +70°C
EP610LC-45	EP610LC-45	LDCC-28, Plastic	0° to +70°C

Specification Number EP610_910_1810-CI (AT) Rev B

Rochester Part Number	Altera Part Number	Package	Temperature
EP610LI-15	EP610LI-15	LDCC-28, Plastic	-40° to +85°C
EP610LI-20	EP610LI-20	LDCC-28, Plastic	-40° to +85°C
EP610LI-20T	EP610LI-20T	LDCC-28, Plastic	-40° to +85°C
EP610LI-25	EP610LI-25	LDCC-28, Plastic	-40° to +85°C
EP610LI-35	EP610LI-35	LDCC-28, Plastic	-40° to +85°C
EP610LI-45	EP610LI-45	LDCC-28, Plastic	-40° to +85°C
EP610PC-15	EP610PC-15	PDIP-24	0° to +70°C
EP610PC-20	EP610PC-20	PDIP-24	0° to +70°C
EP610PC-20T	EP610PC-20T	PDIP-24	0° to +70°C
EP610PC-25	EP610PC-25	PDIP-24	0° to +70°C
EP610PC-25T	EP610PC-25T	PDIP-24	0° to +70°C
EP610PC-30	EP610PC-30	PDIP-24	0° to +70°C
EP610PC-35	EP610PC-35	PDIP-24	0° to +70°C
EP610PC-45	EP610PC-45	PDIP-24	0° to +70°C
EP610PI-15	EP610PI-15	PDIP-24	-40° to +85°C
EP610PI-20	EP610PI-20	PDIP-24	-40° to +85°C
EP610PI-25	EP610PI-25	PDIP-24	-40° to +85°C
EP610PI-30	EP610PI-30	PDIP-24	-40° to +85°C
EP610PI-35	EP610PI-35	PDIP-24	-40° to +85°C
EP610PI-45	EP610PI-45	PDIP-24	-40° to +85°C
EP610SC-15	EP610SC-15	SOP-24, Plastic	0° to +70°C
EP610SC-20	EP610SC-20	SOP-24, Plastic	0° to +70°C
EP610SC-25	EP610SC-25	SOP-24, Plastic	0° to +70°C
EP610SI-25	EP610SI-25	SOP-24, Plastic	-40° to +85°C
EP610SI-30	EP610SI-30	SOP-24, Plastic	-40° to +85°C
EP610SI-35	EP610SI-35	SOP-24, Plastic	-40° to +85°C
EP610SI-45	EP610SI-45	SOP-24, Plastic	-40° to +85°C
EP900ILC-50	EP900ILC-50	LDCC-44, Plastic	0° to +70°C
EP900ILC-50H	EP900ILC-50H	LDCC-44, Plastic	0° to +70°C
EP900IPC-50	EP900IPC-50	PDIP-40	0° to +70°C
EP910DC-25	EP910DC-25	CDIP-40	0° to +70°C
EP910DC-30	EP910DC-30	CDIP-40	0° to +70°C
EP910DC-35	EP910DC-35	CDIP-40	0° to +70°C
EP910DC-45	EP910DC-45	CDIP-40	0° to +70°C
EP910DI-12	EP910DI-12	CDIP-40	-40° to +85°C
EP910DI-15	EP910DI-15	CDIP-40	-40° to +85°C
EP910DI-25	EP910DI-25	CDIP-40	-40° to +85°C
EP910DI-30	EP910DI-30	CDIP-40	-40° to +85°C
EP910DI-35	EP910DI-35	CDIP-40	-40° to +85°C
EP910DI-40	EP910DI-40	CDIP-40	-40° to +85°C
EP910DI-50	EP910DI-50	CDIP-40	-40° to +85°C
EP910IDC-15	EP910IDC-15	CDIP-40	0° to +70°C
EP910IDI-15	EP910IDI-15	CDIP-40	-40° to +85°C
EP910ILC-12	EP910ILC-12	LDCC-44, Plastic	0° to +70°C
EP910ILC-12H	EP910ILC-12H	LDCC-44, Plastic	0° to +70°C
EP910ILC-15	EP910ILC-15	LDCC-44, Plastic	0° to +70°C

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EP910ILC-15H	EP910ILC-15H	LDCC-44, Plastic	0° to +70°C
EP910ILI-12	EP910ILI-12	LDCC-44, Plastic	-40° to +85°C
EP910IPC-12	EP910IPC-12	PDIP-40	0° to +70°C
EP910IPC-25	EP910IPC-25	PDIP-40	0° to +70°C
EP910LC-30	EP910LC-30	LDCC-44, Plastic	0° to +70°C
EP910LC-30T	EP910LC-30T	LDCC-44, Plastic	0° to +70°C
EP910LC-35	EP910LC-35	LDCC-44, Plastic	0° to +70°C
EP910LC-35H	EP910LC-35H	LDCC-44, Plastic	0° to +70°C
EP910LC-40	EP910LC-40	LDCC-44, Plastic	0° to +70°C
EP910LC-40H	EP910LC-40H	LDCC-44, Plastic	0° to +70°C
EP910LI-12	EP910LI-12	LDCC-44, Plastic	-40° to +85°C
EP910LI-15	EP910LI-15	LDCC-44, Plastic	-40° to +85°C
EP910LI-25	EP910LI-25	LDCC-44, Plastic	-40° to +85°C
EP910LI-30	EP910LI-30	LDCC-44, Plastic	-40° to +85°C
EP910LI-35	EP910LI-35	LDCC-44, Plastic	-40° to +85°C
EP910LI-40	EP910LI-40	LDCC-44, Plastic	-40° to +85°C
EP910LI-50	EP910LI-50	LDCC-44, Plastic	-40° to +85°C
EP910PC-30	EP910PC-30	PDIP-40	0° to +70°C
EP910PI-12	EP910PI-12	PDIP-40	-40° to +85°C
EP910PI-15	EP910PI-15	PDIP-40	-40° to +85°C
EP910PI-25	EP910PI-25	PDIP-40	-40° to +85°C
EP910PI-30	EP910PI-30	PDIP-40	-40° to +85°C
EP910PI-35	EP910PI-35	PDIP-40	-40° to +85°C
EP910PI-40	EP910PI-40	PDIP-40	-40° to +85°C
EP910PI-50	EP910PI-50	PDIP-40	-40° to +85°C
EP1810GC-35	EP1810GC-35	PGA-68, Ceramic	0° to +70°C
EP1810GC-45	EP1810GC-45	PGA-68, Ceramic	0° to +70°C
EP1810GC-70	EP1810GC-70	PGA-68, Ceramic	0° to +70°C
EP1810GI-35	EP1810GI-35	PGA-68, Ceramic	-40° to +85°C
EP1810GI-45	EP1810GI-45	PGA-68, Ceramic	-40° to +85°C
EP1810GI-70	EP1810GI-70	PGA-68, Ceramic	-40° to +85°C
EP1810LC-45	EP1810LC-45	LDCC-68, Plastic	0° to +70°C
EP1810LC-45AA	EP1810LC-45AA	LDCC-68, Plastic	0° to +70°C
EP1810LC-45H	EP1810LC-45H	LDCC-68, Plastic	0° to +70°C
EP1810LC-70	EP1810LC-70	LDCC-68, Plastic	0° to +70°C
EP1810LI-35	EP1810LI-35	LDCC-68, Plastic	-40° to +85°C
EP1810LI-45	EP1810LI-45	LDCC-68, Plastic	-40° to +85°C
EP1810LI-70	EP1810LI-70	LDCC-68, Plastic	-40° to +85°C

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Functional Description

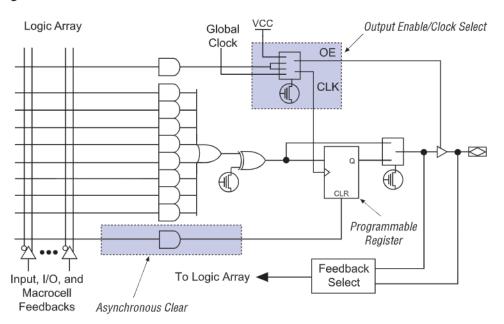
The Classic architecture includes the following elements:

- Macrocells
- Programmable registers
- Output enable/clock select
- Feedback select

Macrocells

Classic macrocells, shown in Figure 1, can be individually configured for both sequential and combinatorial logic operation. Eight product terms form a programmable-AND array that feeds an OR gate for combinatorial logic implementation. An additional product term is used for asynchronous clear control of the internal register; another product term implements either an output enable or a logic-array-generated clock. Inputs to the programmable-AND array come from both the true and complement signals of the dedicated inputs, feedbacks from I/O pins that are configured as inputs, and feedbacks from macrocell outputs. Signals from dedicated inputs are globally routed and can feed the inputs of all device macrocells. The feedback multiplexer controls the routing of feedback signals from macrocells and from I/O pins.

Figure 1. Classic Device Macrocell



The eight product terms of the programmable-AND array feed the 8-input OR gate, which then feeds one input to an XOR gate. The other input to the XOR gate is connected to a programmable bit that allows the array output to be inverted. Altera's MAX+PLUS II software uses the XOR gate to implement either active-high or active-low logic, or De Morgan's inversion to reduce the number of product terms needed to implement a function.

Programmable Registers

To implement registered functions, each macrocell register can be individually programmed for D, T, JK, or SR operation. If necessary, the register can be bypassed for combinatorial operation. During design compilation, the MAX+PLUS II software selects the most efficient register operation for each registered function to minimize the logic resources needed by the design. Registers have an individual asynchronous clear function that is controlled by a dedicated product term. These registers are cleared automatically during power-up.

In addition, macrocell registers can be individually clocked by either a global clock or any input or feedback path to the AND array. Altera's proprietary programmable I/O architecture allows the designer to program output and feedback paths for combinatorial or registered operation in both active-high and active-low modes. These features make it possible to simultaneously implement a variety of logic functions.

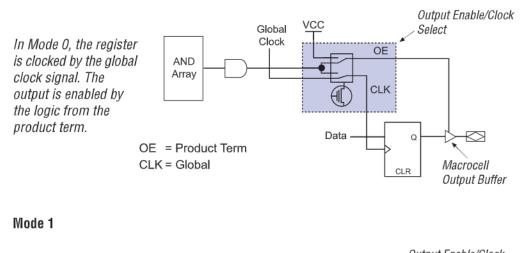
Output Enable/Clock Select

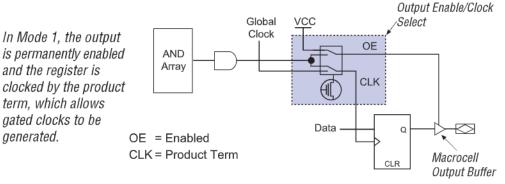
Figure 2 shows the two operating modes (Modes 0 and 1) provided by the output enable/clock (OE/CLK) select. The OE/CLK select, which is controlled by a single programmable bit, can be individually configured for each macrocell. In Mode 0, the tri-state output buffer is controlled by a single product term. If the output enable is high, the output buffer is enabled. If the output enable is low, the output has a high-impedance value. In Mode 0, the macrocell flipflop is clocked by its global clock input signal.

In Mode 1, the output enable buffer is always enabled, and the macrocell register can be triggered by an array clock signal generated by a product term. This mode allows registers to be individually clocked by any signal on the AND array. With both true and complement signals in the AND array, the register can be configured to trigger on a rising or falling edge. This product-term-controlled clock configuration also supports gated clock structures.



Mode O

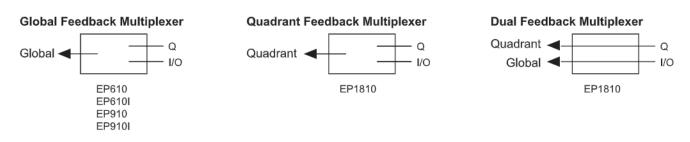




Feedback Select

Each macrocell in a Classic device provides feedback selection that is controlled by the feedback multiplexer. This feedback selection allows the designer to feed either the macrocell output or the I/O pin input associated with the macrocell back into the AND array. The macrocell output can be either the Q output of the programmable register or the combinatorial output of the macrocell. Different devices have different feedback multiplexer configurations. See Figure 3.





EP610, EP610I, EP910, and EP910I devices have a global feedback configuration; either the macrocell output (Q) or the I/O pin input (I/O) can feed back to the AND array so that it is accessible to all other macrocells.

EP1810 macrocells can have either of two feedback configurations: quadrant or dual. Most macrocells in EP1810 devices have a quadrant feedback configuration; either the macrocell output or I/O pin input can feed back to other macrocells in the same quadrant. Selected macrocells in EP1810 devices have a dual feedback configuration: the output of the macrocell feeds back to other macrocells in the same quadrant, and the I/O pin input feeds back to all macrocells in the device. If the associated I/O pin is not used, the macrocell output can optionally feed all macrocells in the device. In this case, the output of the macrocell passes through the tri-state buffer and uses the feedback path between the buffer and the I/O pin.

Design Security Classic devices contain a programmable security bit that controls access to the data programmed into the device. When this bit is programmed, a proprietary design implemented in the device cannot be copied or retrieved. This feature provides a high level of design security because data within configuration elements is invisible. The security bit that controls this function and other program data is reset only when the device is erased.

Timing Model

Device timing can be analyzed with the MAX+PLUS II software, with a variety of popular industry-standard EDA simulators and timing analyzers, or with the timing model shown in Figure 4. Devices have fixed internal delays that allow the user to determine the worst-case timing for any design. The MAX+PLUS II software provides timing simulation, point-to-point delay prediction, and detailed timing analysis for system-level performance evaluation.

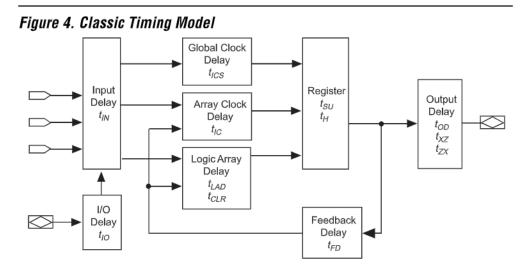
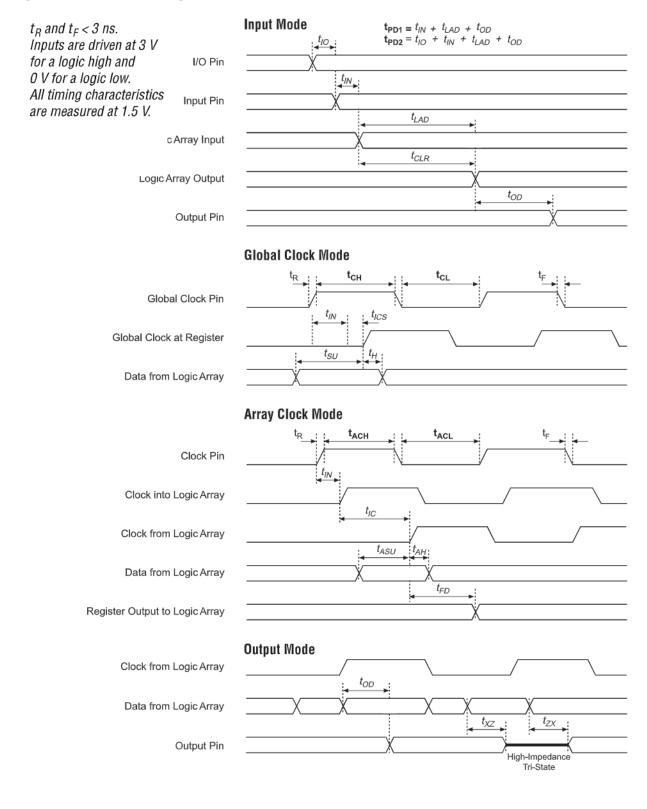


Figure 5. Classic Switching Waveforms

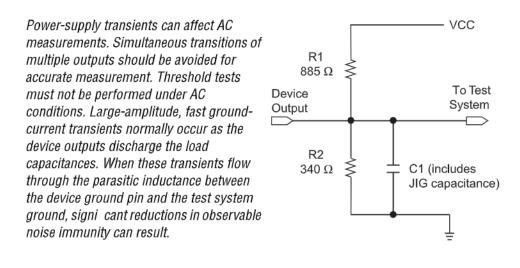


Turbo Bit
OptionMany Classic devices contain a programmable Turbo Bit™ option to
control the automatic power-down feature that enables the low-standby-
power mode. When the Turbo Bit option is turned on, the low-standby-
power mode is disabled. All AC values are tested with the Turbo Bit
option turned on. When the device is operating with the Turbo Bit option
turned off (non-Turbo mode), a non-Turbo adder must be added to the
appropriate AC parameter to determine worst-case timing. The non-
Turbo adder is specified in the "AC Operating Conditions" tables for each
Classic device that supports the Turbo mode.

Generic Testing

Classic devices are fully functionally tested. Complete testing of each programmable EPROM configuration element and all internal logic elements before and after packaging ensures 100% programming yield. See Figure 6 for AC test measurement conditions. These devices also contain on-board logic test circuitry to allow verification of function and AC specifications during standard production flow.

Figure 6. AC Test Conditions



Device Programming

Classic devices can be programmed on 486- and Pentium-based PCs with the MAX+PLUS II Programmer, an Altera Logic Programmer card, the MPU, and the appropriate device adapter. The MPU performs continuity checking to ensure adequate electrical contact between the adapter and the device.



Rochester EPLD devices normally sold in the un-configured state are tested using the original manufacturer's test software to guarantee the data sheet specifications. In some cases, EPLD devices can be configured to the customer's design and fully tested as such.

Notes:

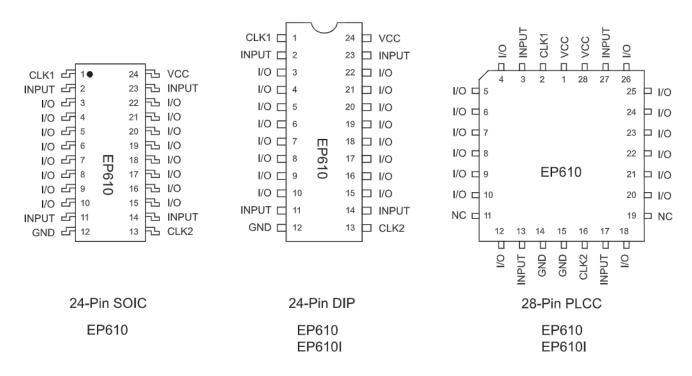
EP610 EPLD

Features

- High-performance, 16-macrocell Classic EPLD
 - Combinatorial speeds with **t**_{PD} as fast as 10 ns
 - Counter frequencies of up to 100 MHz
 - Pipelined data rates of up to 125 MHz
- Programmable I/O architecture with up to 20 inputs or 16 outputs and 2 clock pins
- EP610 and EP610I devices are pin-, function-, and programming file-compatible
- Programmable clock option for independent clocking of all registers
- Macrocells individually programmable as D, T, JK, or SR flipflops, or for combinatorial operation
- Available in the following packages (see Figure 7):
 - 24-pin small-outline integrated circuit (plastic SOIC only)
 - 24-pin ceramic and plastic dual in-line package (CerDIP and PDIP)
 - 28-pin plastic J-lead chip carrier (PLCC)

Figure 7. EP610 Package Pin-Out Diagrams

Package outlines not drawn to scale. Windows in ceramic packages only.



General Description

EP610 devices have 16 macrocells, 4 dedicated input pins, 16 I/O pins, and 2 global clock pins (see Figure 8). Each macrocell can access signals from the global bus, which consists of the true and complement forms of the dedicated inputs and the true and complement forms of either the output of the macrocell or the I/O input. The CLK1 signal is a dedicated global clock input for the registers in macrocells 9 through 16. The CLK2 signal is a dedicated global clock input for registers in macrocells 1 through 8.

Figure 8. EP610 Block Diagram

Numbers without parentheses are for DIP and SOIC packages. Numbers in parentheses are for J-lead packages.

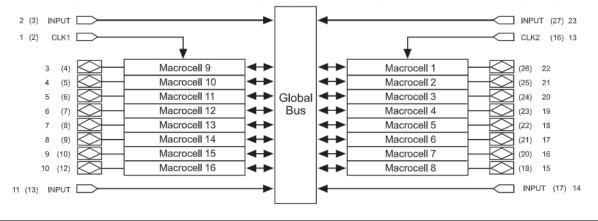
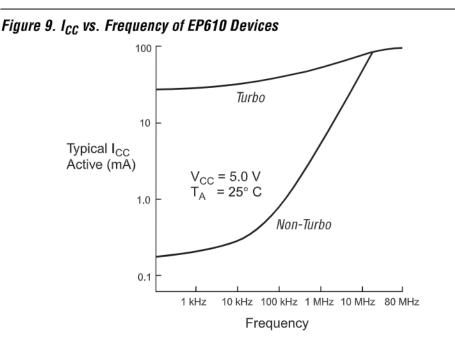
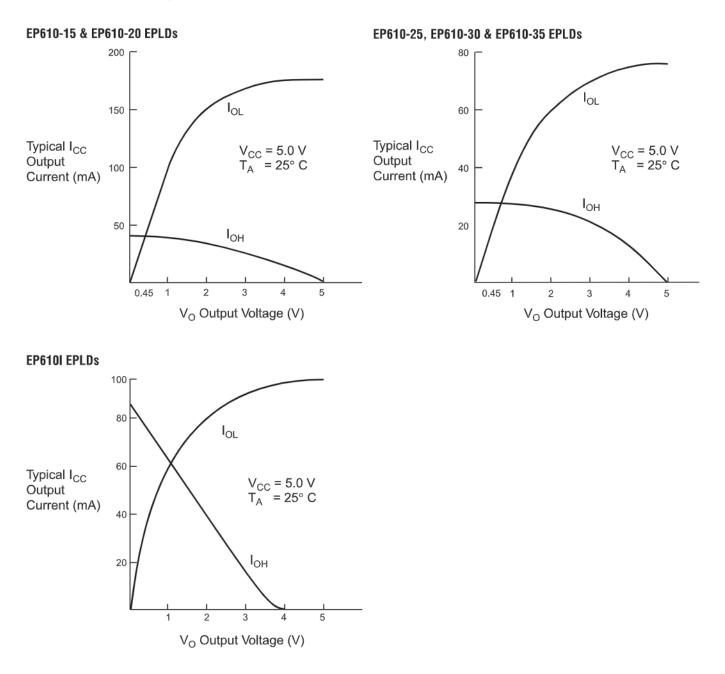


Figure 9 shows the typical supply current (I $_{\rm CC}$) versus frequency of EP610 devices.





Drive characteristics may exceed shown curves.



Operating Conditions

Tables 2 through 7 provide information on absolute maximum ratings, recommended operating conditions, operating conditions, and capacitance for EP610 and EP610I devices.

Symbol	Parameter	Conditions	EP	EP610 EP610I		Unit	
			Min	Max	Min	Max	
V _{CC}	Supply voltage	With respect to ground (2)	-2.0	7.0	-2.0	7.0	V
VI	DC input voltage		-2.0	7.0	-0.5	V _{CC} + 0.5	V
I _{MAX}	DC V _{CC} or ground current		-175	175			mA
I _{OUT}	DC output current, per pin		-25	25			mA
T _{STG}	Storage temperature	No bias	-65	150	-65	150	°C
T _{AMB}	Ambient temperature	Under bias	-65	135	-65	135	°C
Т _Ј	Junction temperature	Ceramic packages, under bias		150		150	°C
		Plastic packages, under bias		135		135	°C

Symbol	Parameter	Conditions	EP	610	EP	Unit	
			Min	Max	Min	Max	
V _{CC}	Supply voltage	(3)	4.75 (4.5)	5.25 (5.5)	4.75	5.25	V
VI	Input voltage		-0.3	V _{CC} + 0.3	-0.3	V _{CC} + 0.3	V
Vo	Output voltage		0	V _{CC}	0	V _{CC}	V
T _A	Operating temperature	For commercial use	0	70	0	70	°C
		For industrial use	-40	85	-40	85	°C
t _R	Input rise time	(4)		100 (50)		500	ns
t _F	Input fall time	(4)		100 (50)		500	ns

Table 4	. EP610 & EP610I Device DC Operat	ing Conditions Note (5)			
Symbol	Parameter	Conditions	Min	Max	Unit
VIH	High-level input voltage		2.0	V _{CC} + 0.3	V
V _{IL}	Low-level input voltage		-0.3	0.8	V
V _{OH}	High-level TTL output voltage	I _{OH} = –4 mA DC <i>(</i> б)	2.4		V
	High-level CMOS output voltage	I _{OH} = -0.6 mA DC <i>(6), (7)</i>	3.84		V
V _{OL}	Low-level output voltage	I _{OL} = 4 mA DC <i>(</i> 6)		0.45	V
II	I/O pin leakage current of dedicated input pins	V _I = V _{CC} or ground	-10	10	μA
I _{OZ}	Tri-state output leakage current	$V_{O} = V_{CC}$ or ground	-10	10	μA

Table 5	Table 5. EP610 & EP610I Device Capacitance Note (8)										
Symbol	Parameter	Conditions	EP610-15 EP610-20				EP61	0-25 0-30 0-35	EP6	610I	Unit
			Min	Max	Min	Max	Min	Max			
C _{IN}	Input pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		10		20		8	pF		
C _{I/O}	I/O pin capacitance	V _{OUT} = 0 V, f = 1.0 MHz		12		20		8	pF		
C _{CLK1}	CLK1 pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		20		20		10	pF		
C _{CLK2}	CLK2 pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		20		50		12	pF		

Table 6. EP610 Device I_{CC} Supply Current Note (1), (9)

Symbol	Parameter				Unit		
			Grade	Min	Тур	Max	
I _{CC1}	V _{CC} supply current (non-Turbo, standby)	V _I = V _{CC} or ground, no load (10), (11)			20	150	μA
I _{CC2}	V _{CC} supply current (non-Turbo, active)	$V_{I} = V_{CC}$ or ground, no load, f = 1.0 MHz (10), (11)			5	10 (15)	mA
I _{CC3}	V _{CC} supply current	$V_{I} = V_{CC}$ or ground, no load,	-15, -20		60	90 (115)	mA
	(Turbo, active)	f = 1.0 MHz (11)	-25, -30, -35		45	60 (75)	mA

Table 7. EP610I Device I_{CC} Supply Current Note (9)

Symbol	Parameter	Conditions	EP610I			Unit
			Min	Тур	Max	
I _{CC1}	V _{CC} supply current (non-Turbo, standby)	V _I = V _{CC} or ground, no load, (10), (11)		20	150	μA
I _{CC2}	V _{CC} supply current (non-Turbo, active)	$V_{I} = V_{CC}$ or ground, no load, f = 1.0 MHz (10), (11)		3	8	mA
I _{CC3}	V _{CC} supply current (Turbo, active)	$V_I = V_{CC}$ or ground, no load, f = 1.0 MHz (11)		65	105	mA

- (1) Numbers in parentheses are for industrial-temperature-range devices.
- (2) The minimum DC input is -0.3 V. During transitions, the inputs may undershoot to -2.0 V (EP610) or -0.5 V (EP610I) or overshoot to 7.0 V (EP610) or V_{CC} + 0.5 V (EP610I) for input currents less than 100 mA and periods less than 20 ns.
- (3) For EP610 devices, maximum V_{CC} rise time is 50 ms. For EP610I devices, maximum V_{CC} rise time is unlimited with monotonic rise.
- (4) For EP610-15 and EP610-20 devices: t_R and $t_F = 40$ ns. For EP610-15 and EP610-20 clocks: t_R and $t_F = 20$ ns.
- (5) These values are specified in Table 3
- (6) The I_{OH} parameter refers to high-level TTL or CMOS output current; the I_{OL} parameter refers to low-level TTL output current.
- (7) This parameter does not apply to EP610I devices.
- (8) The device capacitance is measured at 25° C and is sample-tested only.
- (9) Typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5 V$.
- (10) When the Turbo Bit option is not set (non-Turbo mode), EP610 devices enter standby mode if no logic transitions occur for 100 ns after the last transition. When the Turbo Bit option is not set, EP610I devices enter standby mode if no logic transitions occur for 75 ns after the last transition.
- (11) Measured with a device programmed as a 16-bit counter.

Table 8	8. EP610-15 & EP610-20 Externa	I Timing Parameters	No	tes (1))			
Symbol	Parameter	Conditions	EP61	0-15	EP61	0-20	Non-Turbo Adder	Unit
			Min	Max	Min	Max	(2)	
t _{PD1}	Input to non-registered output	C1 = 35 pF		15.0		20.0	20.0	ns
t _{PD2}	I/O input to non-registered output	C1 = 35 pF		17.0		22.0	20.0	ns
t _{PZX}	Input to output enable	C1 = 35 pF		15.0		20.0	20.0	ns
t _{PXZ}	Input to output disable	C1 = 5 pF (3)		15.0		20.0	20.0	ns
t _{CLR}	Asynchronous output clear time	C1 = 35 pF		15.0		20.0	20.0	ns
f _{MAX}	Maximum clock frequency	(4)	83.3		62.5		0.0	MHz
t _{SU}	Global clock input setup time		9.0		11.0		20.0	ns
t _H	Global clock input hold time		0.0		0.0		0.0	ns
t _{CH}	Global clock high time		6.0		8.0		0.0	ns
t _{CL}	Global clock low time		6.0		8.0		0.0	ns
t _{CO1}	Global clock to output delay			11.0		13.0	0.0	ns
t _{CNT}	Global clock minimum period			12.0		16.0	0.0	ns
f _{CNT}	Maximum internal global clock frequency	(5)	83.3		62.5		0.0	MHz
t _{ASU}	Array clock input setup time		6.0		8.0		20.0	ns
t _{AH}	Array clock input hold time		6.0		8.0		0.0	ns
t _{ACH}	Array clock high time		7.0		9.0		0.0	ns
t _{ACL}	Array clock low time		7.0		9.0		0.0	ns
t _{ODH}	Output data hold time after clock	C1 = 35 pF (6)	1.0		1.0		1.0	ns
t _{ACO1}	Array clock to output delay			15.0		20.0	20.0	ns
t _{ACNT}	Array clock minimum period			14.0		18.0	0.0	ns
f _{acnt}	Array clock internal maximum frequency	(5)	71.4		55.6		0.0	MHz

Table 9	Table 9. EP610-15 & EP610-20 Internal Timing Parameters (Part 1 of 2)									
Symbol	Parameter	Conditions	EP61	EP610-15 EP610-2		EP610-20				
			Min	Max	Min	Max				
t _{IN}	Input pad and buffer delay			4.0		4.0	ns			
t _{IO}	I/O input pad and buffer delay			2.0		2.0	ns			
t _{LAD}	Logic array delay			6.0		11.0	ns			
t _{OD}	Output buffer and pad delay	C1 = 35 pF		5.0		5.0	ns			
t _{ZX}	Output buffer enable delay	C1 = 35 pF		5.0		5.0	ns			
t_{XZ}	Output buffer disable delay	C1 = 5 pF		5.0		5.0	ns			

Table 9	Table 9. EP610-15 & EP610-20 Internal Timing Parameters (Part 2 of 2)									
Symbol	Parameter	Conditions EP610-15 EP610-2		610-15 EP61		0-20	Unit			
			Min	Max	Min	Max				
t _{SU}	Register setup time		5.0		4.0		ns			
t _H	Register hold time		4.0		7.0		ns			
t _{IC}	Array clock delay			6.0		11.0	ns			
t _{ICS}	Global clock delay			2.0		4.0	ns			
t _{FD}	Feedback delay			1.0		1.0	ns			
t _{CLR}	Register clear time			6.0		11.0	ns			

Tables 10 and 11 show the timing parameters for EP610-25, EP610-30 and EP610-35 devices.

Table 1	Table 10. EP610-25, EP610-30 & EP610-35 External Timing Parameters Notes (1)											
Symbol	Parameter	Conditions	EP61	0-25	EP61	0-30	EP61	0-35	Non-Turbo Adder	Unit		
			Min	Max	Min	Max	Min	Max	(2)			
t _{PD1}	Input to non-registered output	C1 = 35 pF		25.0		30.0		35.0	30.0	ns		
t _{PD2}	I/O input to non-registered output			27.0		32.0		37.0	30.0	ns		
t _{PZX}	Input to output enable			25.0		30.0		35.0	30.0	ns		
t _{PXZ}	Input to output disable	C1 = 5 pF (3)		25.0		30.0		35.0	30.0	ns		
t _{CLR}	Asynchronous output clear time	C1 = 35 pF		27.0		32.0		37.0	30.0	ns		
f _{MAX}	Maximum frequency	(4)	47.6		41.7		37.0		0.0	MHz		
t _{SU}	Global clock input setup time		21.0		24.0		27.0		30.0	ns		
t _H	Global clock input hold time		0.0		0.0		0.0		0.0	ns		
t _{CH}	Global clock high time		10.0		11.0		12.0		0.0	ns		
t _{CL}	Global clock low time		10.0		11.0		12.0		0.0	ns		
t _{CO1}	Global clock to output delay			15.0		17.0		20.0	0.0	ns		
t _{CNT}	Global clock minimum period			25.0		30.0		35.0	0.0	ns		
f _{CNT}	Maximum internal global clock frequency	(5)	40.0		33.3		28.6		0.0	MHz		
t _{ASU}	Array clock input setup time		8.0		8.0		8.0		30.0	ns		
t _{AH}	Array clock input hold time		12.0		12.0		12.0		0.0	ns		
t _{ACH}	Array clock high time		10.0		11.0		12.0		0.0	ns		
t _{ACL}	Array clock low time		10.0		11.0		12.0		0.0	ns		
t _{ODH}	Output data hold time after clock	C1 = 35 pF (6)	1.0		1.0		1.0			ns		
t _{ACO1}	Array clock to output delay			27.0		32.0		37.0	30.0	ns		
t _{ACNT}	Array clock minimum period			25.0		30.0		35.0	0.0	ns		
f _{acnt}	Maximum internal global clock frequency	(5)	40.0		33.3		28.6		0.0	MHz		

Table 1	Table 11. EP610-25, EP610-30 & EP610-35 Internal Timing Parameters											
Symbol	Parameter	Condition	EP610-25		EP610-30		EP610-35		Unit			
			Min	Max	Min	Мах	Min	Max	1			
t _{IN}	Input pad and buffer delay			8.0		9.0		11.0	ns			
t _{IO}	I/O input pad and buffer delay			2.0		2.0		2.0	ns			
t _{LAD}	Logic array delay			11.0		14.0		15.0	ns			
t _{OD}	Output buffer and pad delay	C1 = 35 pF		6.0		7.0		9.0	ns			
t_{ZX}	Output buffer enable delay	C1 = 35 pF		6.0		7.0		9.0	ns			
t _{XZ}	Output buffer disable delay	C1 = 5 pF		6.0		7.0		9.0	ns			
t _{SU}	Register setup time		11.0		11.0		12.0		ns			
t _H	Register hold time		10.0		10.0		10.0		ns			
t _{IC}	Array clock delay			13.0		16.0		17.0	ns			
t _{ICS}	Global clock delay			1.0		1.0		0.0	ns			
t _{FD}	Feedback delay			3.0		5.0		8.0	ns			
t _{CLR}	Register clear time			13.0		16.0		17.0	ns			

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Notes to tables:

- (1) These values are specified in Table 3
- The non-Turbo adder must be added to this parameter when the Turbo Bit option is off. (2)
- (3) Sample-tested only for an output change of 500 mV.
- (4) The f_{MAX} values represent the highest frequency for pipelined data.
- (5) Measured with a device programmed as a 16-bit counter.
- (6) Sample-tested only. This parameter is a guideline based on extensive device characterization. This parameter applies for both global and array clocking.

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Table 12	2. EP610I External Timing Par	ameters	Votes (1)						
Symbol	Parameter	Conditions	EP61	0I-10	EP61	0I-12	EP61	0I-1 5	Non-Turbo Adder	Unit
			Min	Max	Min	Max	Min	Max	(2)	
t _{PD1}	Input to non-registered output	C1 = 35 pF		10.0		12.0		15.0	25.0	ns
t _{PD2}	I/O input to non-registered output			10.0		12.0		15.0	25.0	ns
t _{PZX}	Input to output enable			15.0		15.0		18.0	25.0	ns
t _{PXZ}	Input to output disable	C1 = 5 pF (3)		13.0		15.0		18.0	25.0	ns
t _{CLR}	Asynchronous output clear time	C1 = 35 pF		13.0		15.0		18.0	25.0	ns
f _{MAX}	Maximum frequency	(4)	125.0		100. 0		83.3		0.0	MHz
t _{SU}	Global clock input setup time		7.0		9.0		12.0		25	ns
t _H	Global clock input hold time		0.0		0.0		0.0		0.0	ns
t _{CH}	Global clock high time		5.0		5.0		5.0		0.0	ns
t _{CL}	Global clock low time		5.0		5.0		5.0		0.0	ns
t _{CO1}	Global clock to output delay			6.5		8.0		8.0	0.0	ns
t _{CNT}	Global clock minimum period			10.0		12.0		15.0	25.0	ns
f _{CNT}	Maximum internal global clock frequency	(5)	100.0		83.3		66.0		0.0	MHz
t _{ASU}	Array clock input setup time		1.5		3.0		4.0		25.0	ns
t _{AH}	Array clock input hold time		5.5		6.0		6.0		0.0	ns
t _{ACH}	Array clock high time		5.0		5.0		6.0		0.0	ns
t _{ACL}	Array clock low time		5.0		5.0		6.0		0.0	ns
t _{odh}	Output data hold time after clock	C1 = 35 pF (6)	1.0		1.0		1.0			ns
t _{ACO1}	Array clock to output delay			12.0		14.0		16.0	25.0	ns
t _{ACNT}	Array clock minimum period			10.0		12.0		15.0	25.0	ns
f _{acnt}	Maximum internal array clock frequency	(5)	100.0		83.3		66.0		0.0	MHz

Table 13.	EP610 Internal Timing Para	nmeters							
Symbol	Parameter	Conditions	EP61	EP610I-10		EP610I-12		EP610I-15	
			Min	Max	Min	Max	Min	Max	
t _{IN}	Input pad and buffer delay			1.5		4.0		4.0	ns
t _{IO}	I/O input pad and buffer delay			0.0		0.0		0.0	ns
t _{LAD}	Logic array delay			5.5		6.0		9.0	ns
t _{OD}	Output buffer and pad delay	C1 = 35 pF		3.0		2.0		2.0	ns
t _{ZX}	Output buffer enable delay	C1 = 35 pF		8.0		5.0		6.0	ns
t _{XZ}	Output buffer disable delay	C1 = 5 pF		6.0		5.0		6.0	ns
t _{SU}	Register setup time		3.5		5.0		5.0		ns
t _H	Register hold time		3.5		4.0		7.0		ns
t _{IC}	Array clock delay			7.5		8.0		10.0	ns
t _{ICS}	Global clock delay			2.0		2.0		2.0	ns
t _{FD}	Feedback delay			1.0		1.0		1.0	ns
t _{CLR}	Register clear time			8.5		9.0		12.0	ns

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Notes to tables:

- These values are specified in Table 3 (1)
- (2) The non-Turbo adder must be added to this parameter when the Turbo Bit option is off.
- (3) Sample-tested only for an output change of 500 mV.
- (4) The f_{MAX} values represent the highest frequency for pipelined data.
- Measured with a device programmed as a 16-bit counter. (5)
- (6) Sample-tested only. This parameter is a guideline based on extensive device characterization. This parameter applies for both global and array clocking.



Rochester EPLD devices normally sold in the un-configured state are tested using the original manufacturer's test software to guarantee the data sheet specifications. In some cases, EPLD devices can be configured to the customer's design and fully tested as such.

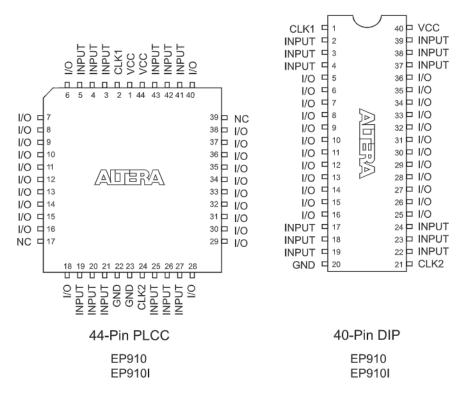
Notes:

EP910 EPLD

Features

- High-performance, 24-macrocell Classic EPLD
 - Combinatorial speeds with **t**_{PD} as fast as 12 ns
 - Counter frequencies of up to 76.9 MHz
 - Pipelined data rates of up to 125 MHz
- Programmable I/O architecture with up to 36 inputs or 24 outputs
- EP910 and EP910I devices are pin-, function-, and programming filecompatible
- Programmable clock option for independent clocking of all registers
- Macrocells individually programmable as D, T, JK, or SR flipflops, or for combinatorial operation
- Available in the following packages (see Figure 11)
 - 44-pin plastic J-lead chip carrier (PLCC)
 - 40-pin ceramic and plastic dual in-line packages (CerDIP and PDIP)





Package outlines are not drawn to scale. Windows in ceramic packages only.

General Description

EP910 devices can implement up to 450 usable gates of SSI and MSI logic functions. EP910 devices have 24 macrocells, 12 dedicated input pins, 24 I/O pins, and 2 global clock pins. Each macrocell can access signals from the global bus, which consists of the true and complement forms of the dedicated inputs and the true complement forms of either the output of the macrocell or the I/O input. The CLK1 and CLK2 signals are the dedicated clock inputs for the registers in macrocells 13 through 24 and 1 through 12, respectively.

Figure 12. EP910 Block Diagram

Numbers without parentheses are for DIP packages. Numbers in parentheses are for J-lead packages.

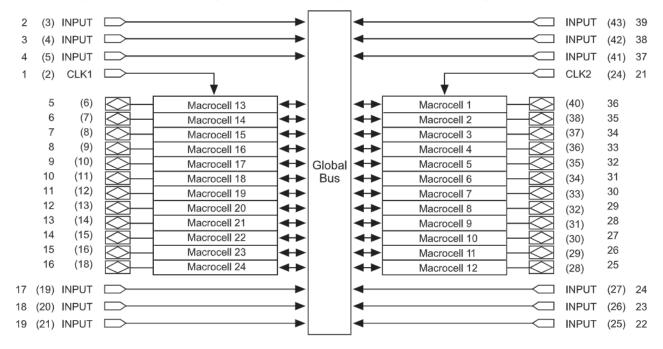


Figure 13. I_{CC} vs. Frequency of EP910 Devices

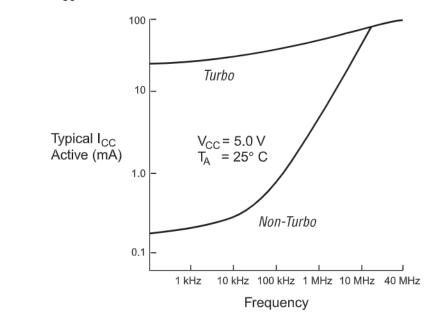
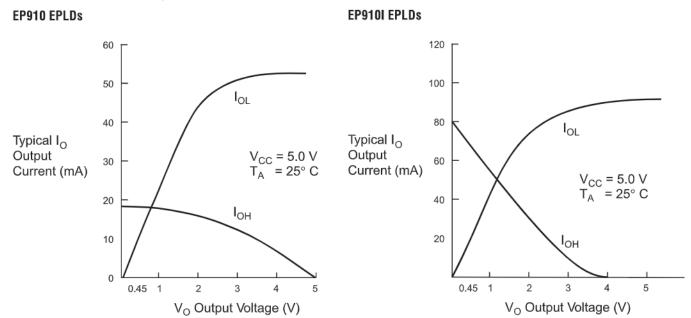


Figure 14 shows the typical output drive characteristics of EP910 devices.



Drive characteristics may exceed shown curves.



Specification Number EP610_910_1810-CI (AT) Rev B

Operating Conditions

Tables 14 through 18 provide information on absolute maximum ratings, recommended operating conditions, operating conditions, and capacitance for EP910 and EP910I devices.

Table 1	4. EP910 & EP910I Device Ab	solute Maximum Ratings	Notes	s (1)			
Symbol	Parameter	Conditions EP910 EP910I				910I	Unit
			Min	Max	Min	Max	
V _{CC}	Supply voltage	With respect to ground (2)	-2.0	7.0	-2.0	7.0	V
VI	DC input voltage		-2.0	7.0	-0.5	V _{CC} + 0.5	V
I _{MAX}	DC V_{CC} or ground current		-250	250			mA
I _{OUT}	DC output current, per pin		-25	25			mA
T _{STG}	Storage temperature	No bias	-65	150	-65	150	°C
T _{AMB}	Ambient temperature	Under bias	-65	135	-65	135	°C
TJ	Junction temperature	Ceramic packages, under bias		150		150	°C
		Plastic packages, under bias		135		135	°C

Table 15. EP910 & EP910I Device Recommended Operating Conditions Notes (1)										
Symbol	Parameter	Conditions	EP	910	EP	Unit				
			Min	Min Max		Max	1			
V _{CC}	Supply voltage	(3)	4.75 (4.5)	5.25 (5.5)	4.75	5.25	V			
VI	Input voltage		-0.3	V _{CC} + 0.3	-0.3	V _{CC} + 0.3	V			
Vo	Output voltage		0	V _{CC}	0	V _{CC}	V			
T _A	Operating temperature	For commercial use	0	70	0	70	°C			
		For industrial use	-40	85			°C			
t _R	Input rise time	(4)		100 (50)		500	ns			
t _F	Input fall time	(4)		100 (50)		500	ns			

 Table 16. EP910 & EP910I Device DC Operating Conditions
 Notes (5), (6)

Symbol	Parameter	Conditions	Min	Max	Unit
VIH	High-level input voltage		2.0	V _{CC} + 0.3	V
V _{IL}	Low-level input voltage		-0.3	0.8	V
V _{OH}	High-level TTL output voltage	I _{OH} =4 mA DC (7)	2.4		V
	High-level CMOS output voltage	I _{OH} = –0.6 mA DC <i>(7), (8)</i>	3.84		V
V _{OL}	Low-level output voltage	I _{OL} = 4 mA DC <i>(7)</i>		0.45	V
I _I	I/O leakage current of dedicated input pins	$V_{I} = V_{CC}$ or ground	-10	10	μA
I _{OZ}	Tri-state output leakage current	$V_{O} = V_{CC}$ or ground	-10	10	μA

Table 1	Table 17. EP910 & EP910I Device Capacitance Notes (5)										
Symbol	Parameter	Conditions	EP	910	EP9	101	Unit				
			Min	Max	Min	Max					
C _{IN}	Input pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		20		8	pF				
C _{I/O}	I/O pin capacitance	V _{OUT} = 0 V, f = 1.0 MHz		20		8	pF				
C _{CLK1}	CLK1 pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		20		10	pF				
C _{CLK2}	CLK2 pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		60		12	pF				

Table 18. EP910 & EP910I Device I _{cc} Supply Current	Notes (1), (5), (6)
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Symbol	Parameter	Conditions		EP910 EP910I		I	Unit		
			Min	Тур	Max	Min	Тур	Max	
I _{CC1}	V _{CC} supply current (non-Turbo, standby)	V _I = V _{CC} or ground, no load (9), (10)		20	150		60	150	μA
I _{CC2}	V _{CC} supply current (non-Turbo, active)	$V_{I} = V_{CC}$ or ground, no load, f = 1.0 MHz (9), (10)		6	20		4	12	mA
I _{CC3}	V _{CC} supply current (Turbo, active)	$V_I = V_{CC}$ or ground, no load, f = 1.0 MHz (10)		45	80 (100)		120	150	mA

- (1) Numbers in parentheses are for industrial-temperature-range devices.
- (2) The minimum DC input is -0.3 V. During transitions, the inputs may undershoot to -2.0 V (EP910) or
- (3) -0.5 V (EP910I) or overshoot to 7.0 V (EP910) or V_{CC} + 0.5 V (EP910I) for input currents less than 100 mA and periods less than 20 ns.

Maximum V_{CC} rise time for EP910 devices = 50 ms; for EP910I devices, maximum V_{CC} rise time is unlimited with (4) monotonic rise.

- For all clocks: t_R and t_F = 100 ns (50 ns for the industrial-temperature-range version).
- (5) These values are specified in Table 15
- (6) The device capacitance is measured at 25° C and is sample-tested only.
- (7) The I_{OH} parameter refers to high-level TTL or CMOS output current; the I_{OL} parameter refers to low-level TTL
- (8) output current. This parameter does not apply to EP910I devices
- This parameter does not apply to EP910I devices.
- (9) When the Turbo Bit option is not set (non-Turbo mode), an EP910 device will enter standby mode if no logic
- (10) transitions occur for 100 ns after the last transition, and an EP910I device will enter standby mode if no logic transitions occur for 75 ns after the last transition.
 Magnute device programmed as a 24 bit counter.

Measured with a device programmed as a 24-bit counter.

Table 1	Table 19. EP910 External Timing Parameters Notes (1)											
Symbol	Parameter	Conditions	EP91	0-30	EP91	0-35	EP91	0-40	Non-	Unit		
			Min	Max	Min	Max	Min	Max	Turbo Adder (2)			
t _{PD1}	Input to non-registered output	C1 = 35 pF		30.0		35.0		40.0	30.0	ns		
t _{PD2}	I/O input to non-registered output	C1 = 35 pF		33.0		38.0		43.0	30.0	ns		
t _{PZX}	Input to output enable	C1 = 35 pF		30.0		35.0		40.0	30.0	ns		
t _{PXZ}	Input to output disable	C1 = 5 pF (3)		30.0		35.0		40.0	30.0	ns		
t _{CLR}	Asynchronous output clear time	C1 = 35 pF		33.0		38.0		43.0	30.0	ns		
f _{MAX}	Maximum frequency	(4)	41.7		37.0		32.3		0.0	MHz		
t _{su}	Global clock input setup time		24.0		27.0		31.0		30.0	ns		
t _H	Global clock input hold time		0.0		0.0		0.0		0.0	ns		
t _{CH}	Global clock high time		12.0		13.0		15.0		0.0	ns		
t _{CL}	Global clock low time		12.0		13.0		15.0		0.0	ns		
t _{CO1}	Global clock to output delay	C1 = 35 pF		18		21.0		24.0	0.0	ns		
t _{CNT}	Global clock minimum clock period	(5)		30.0		35.0		40.0	0.0	ns		
f _{CNT}	Maximum internal global clock frequency	(5)	33.3		28.6		25.0		0.0	MHz		
t _{ASU}	Array clock input setup time		10.0		10.0		10.0		30.0	ns		
t _{AH}	Array clock input hold time		15.0		15.0		15.0		0.0	ns		
t _{ACH}	Array clock high time		15.0		16.0		17.0		0.0	ns		
t _{ACL}	Array clock low time		15.0		16.0		17.0		0.0	ns		
t _{ODH}	Output data hold time after clock	C1 = 35 pF(6)	1.0		1.0		1.0			ns		
t _{ACO1}	Array clock to output delay	C1 = 35 pF		33.0		38.0		43.0	30.0	ns		
t _{ACNT}	Array clock minimum clock period			30.0		35.0		40.0	0.0	ns		
f _{acnt}	Maximum internal array clock frequency	(5)	33.3		28.6		25.0		0.0	MHz		

Table 20. EP910 Internal Timing Parameters											
Symbol	Parameter	Condition	EP91	EP910-30		0-35	EP910-40		Unit		
	Falanicici	Condition	Min	Max	Min	Max	Min	Max			
t _{IN}	Input pad and buffer delay			9.0		10.0		13.0	ns		
t _{IO}	I/O input pad and buffer delay			3.0		3.0		3.0	ns		
t_{LAD}	Logic array delay			14.0		16.0		17.0	ns		
t _{OD}	Output buffer and pad delay	C1 = 35 pF		7.0		9.0		10.0	ns		
t_{ZX}	Output buffer enable delay	C1 = 35 pF		7.0		9.0		10.0	ns		
t_{XZ}	Output buffer disable delay	C1 = 5 pF		7.0		9.0		10.0	ns		
t _{SU}	Register setup time		12.0		13.0		15.0		ns		
t _H	Register hold time		12.0		12.0		12.0		ns		
t _{IC}	Array clock delay			17.0		19.0		20.0	ns		
t _{ICS}	Global clock delay			2.0		2.0		1.0	ns		
t _{FD}	Feedback delay			4.0		6.0		8.0	ns		
t _{CLR}	Register clear time			17.0		19.0		20.0	ns		

- (1) These values are specified in Table 15
- (2) The non-Turbo adder must be added to this parameter when the Turbo Bit option is off.
- (3) Sample-tested only for an output change of 500 mV.
- (4) The f_{MAX} values represent the highest frequency for pipelined data.
- (5) Measured with a device programmed as a 24-bit counter.
- (6) Sample-tested only. This parameter is a guideline based on extensive device characterization and applies for both global and array clocking.

Table 21. EP910I External Timing Parameters Notes (1)										
Symbol	Parameter	Conditions	EP910I-12		EP910I-15		EP910I-25		Non-Turbo Adder	Unit
			Min	Max	Min	Max	Min	Max	(2)	1
t _{PD1}	Input to non-registered output	C1 = 35 pF		12.0		15.0		25.0	40.0	ns
t _{PD2}	I/O input to non-registered output	C1 = 35 pF		12.0		15.0		25.0	40.0	ns
t _{PZX}	Input to output enable	C1 = 35 pF		15.0		18.0		28.0	40.0	ns
t _{PXZ}	Input to output disable	C1 = 35 pF (3)		15.0		18.0		28.0	40.0	ns
t _{CLR}	Asynchronous output clear time	C1 = 35 pF		15.0		18.0		28.0	40.0	ns
f _{MAX}	Global clock maximum frequency	(4)	125.0		100.0		62.5		0.0	MHz
t _{su}	Global clock input setup time		8.0		11.0		16.0		40.0	ns
t _H	Global clock input hold time		0.0		0.0		0.0		0.0	ns
t _{CH}	Global clock high time		5.0		6.0		10.0		0.0	ns
t _{CL}	Global clock low time		5.0		6.0		10.0		0.0	ns
t _{CO1}	Global clock to output delay			8.0		9.0		14.0	0.0	ns
t _{CNT}	Global clock minimum clock period	C1 = 35 pF		13.0		15.0		25.0	40.0	ns
f _{CNT}	Maximum internal global clock frequency	(5)	76.9		66.6		40.0		0.0	MHz
t _{ASU}	Array clock input setup time		3.0		4.0		8.0		40.0	ns
t _{AH}	Array clock input hold time		6.0		7.0		8.0			ns
t _{ACH}	Array clock high time		6.0		7.5		12.5			ns
t _{ACL}	Array clock low time		6.0		7.5		12.5			ns
t _{odh}	Output data hold time after clock	C1 = 35 pF (6)	1.0		1.0		1.0			ns
t _{ACO1}	Array clock to output delay	C1 = 35 pF		16.0		18.0		22.0	40.0	ns
t _{ACNT}	Array clock minimum clock period			13.0		15.0		25.0	40.0	ns
f _{acnt}	Maximum internal array clock frequency	(5)	76.9		66.6		40.0			MHz

Table 22. EP910I Internal Timing Parameters										
Symbol	Parameter	Condition	EP910I-12		EP910I-15		EP910I-25		Unit	
			Min	Max	Min	Max	Min	Max		
t _{IN}	Input pad and buffer delay			2.0		3.0		2.0	ns	
t _{IO}	I/O input pad and buffer delay			0.0		0.0		0.0	ns	
t _{LAD}	Logic array delay			8.0		9.0		17.0	ns	
t _{OD}	Output buffer and pad delay	C1 = 35 pF		2.0		3.0		6.0	ns	
t _{ZX}	Output buffer enable delay	C1 = 35 pF		5.0		6.0		9.0	ns	
t _{XZ}	Output buffer disable delay	C1 = 5 pF		5.0		6.0		9.0	ns	
t _{SU}	Register setup time		4.0		5.0		5.0		ns	
t _H	Register hold time		4.0		6.0		11.0		ns	
t _{IC}	Array clock delay			12.0		12.0		14.0	ns	
t _{ICS}	Global clock delay			4.0		3.0		6.0	ns	
t _{FD}	Feedback delay			1.0		1.0		3.0	ns	
t _{CLR}	Register clear time			11.0		12.0		20.0	ns	

- (1) These values are specified in Table 15
- (2) The non-Turbo adder must be added to this parameter when the Turbo Bit option is off.
- (3) Sample-tested only for an output change of 500 mV.
- (4) The f_{MAX} values represent the highest frequency for pipelined data.
- (5) Measured with a device programmed as a 24-bit counter.
- (6) Sample-tested only. This parameter is a guideline based on extensive device characterization and applies for both global and array clocking.



Rochester EPLD devices normally sold in the un-configured state are tested using the original manufacturer's test software to guarantee the data sheet specifications. In some cases, EPLD devices can be configured to the customer's design and fully tested as such.

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EP1810 EPLD

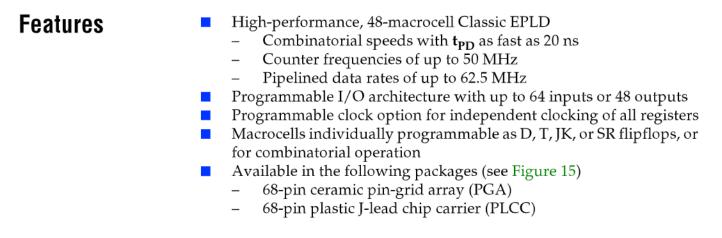
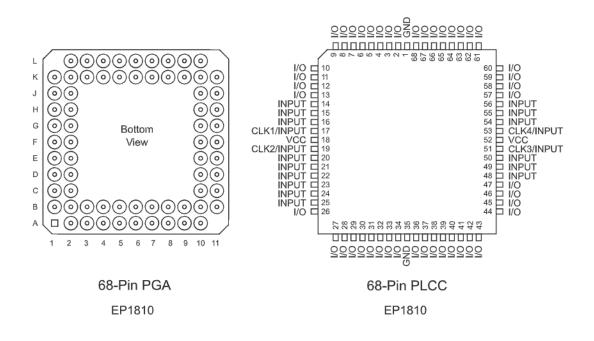


Figure 15. EP1810 Package Pin-Out Diagrams

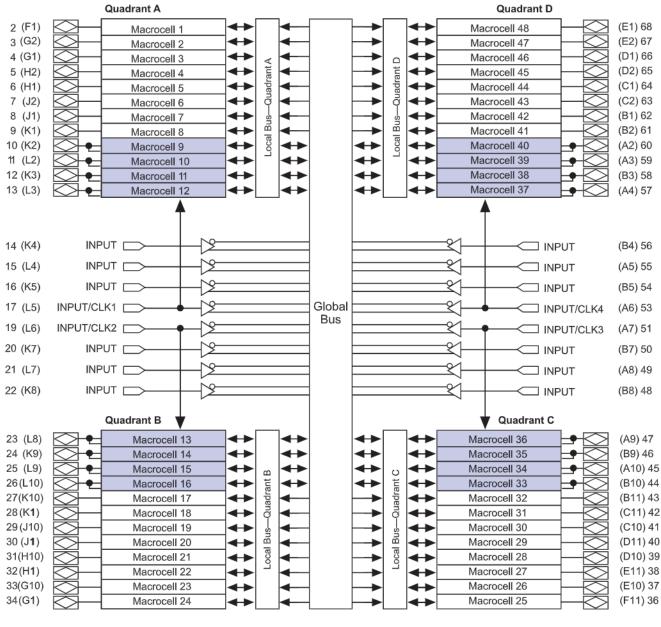


General Description

The EP1810 device offers LSI density, TTL-equivalent speed, and low-power consumption. EP1810 devices have 48 macrocells, 16 dedicated input pins, and 48 I/O pins. EP1810 devices are divided into four quadrants, each containing 12 macrocells. Of the 12 macrocells in each quadrant, 8 have quadrant feedback and are "local" macrocells. The remaining 4 macrocells in the quadrant are "global" macrocells. Both local and global macrocells can access signals from the global bus, which consists of the true and complement forms of the dedicated inputs and the true and complement forms of the feedbacks from the global macrocells.

EP1810 devices also have four dedicated inputs (one in each quadrant) that can be used as quadrant clock inputs. If the dedicated input is used as a clock pin, the input feeds the clock input of all registers in that particular quadrant.

Figure 16. EP1810 Block Diagram



Pin numbers are for J-lead packages. Pin numbers in parentheses are for PGA packages.

Global Macrocells

Local Macrocells

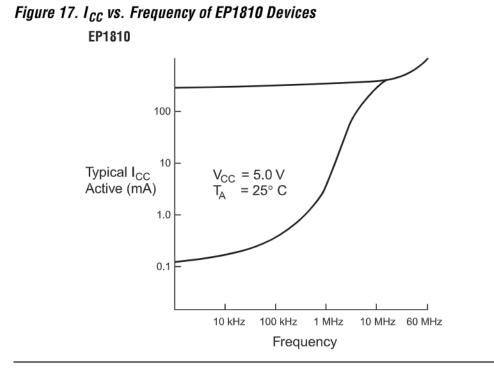
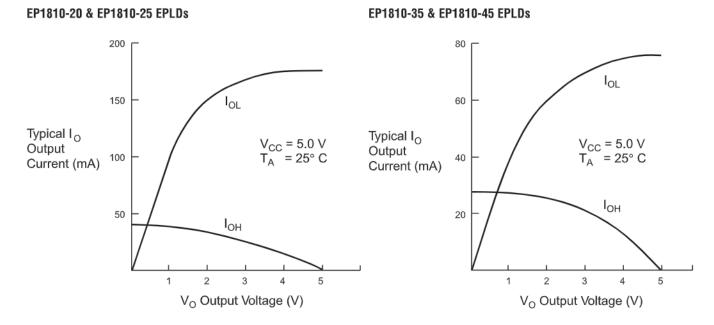


Figure 18 shows the output drive characteristics of EP1810 devices.

Figure 18. Output Drive Characteristics of EP1810 Devices

Drive characteristics may exceed shown curves.



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Operating Conditions

Tables 23 through 27 provide information on absolute maximum ratings, recommended operating conditions, operating conditions, and capacitance for EP1810 devices.

Table 2	Table 23. EP1810 Device Absolute Maximum Ratings Notes (1)									
Symbol	Parameter	Conditions	Min	Max	Unit					
V _{CC}	Supply voltage	With respect to ground (2)	-2.0 (-0.5)	7.0	V					
V_{I}	DC input voltage	With respect to ground (2)	-2.0 (-0.5)	7.0	V					
I _{MAX}	DC V_{CC} or ground current		-300 (-400)	300 (400)	mA					
I _{OUT}	DC output current, per pin		-25	25	mA					
T _{STG}	Storage temperature	No bias	-65	150	°C					
T _{AMB}	Ambient temperature	Under bias	-65	135	°C					
TJ	Junction temperature	Ceramic packages, under bias		150	°C					
		Plastic packages, under bias		135	°C					

 Table 24. EP1810 Device Recommended Operating Conditions
 Notes (1)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	Supply voltage	(3)	4.75 (4.5)	5.25 (5.5)	V
VI	Input voltage		-0.3	V _{CC} + 0.3	V
Vo	Output voltage		0	V _{CC}	V
T _A	Operating temperature	For commercial use	0	70	°C
		For industrial use	-40	85	°C
t _R	Input rise time	(4)		50	ns
t _F	Input fall time	(4)		50	ns

Table 2	Table 25. EP1810 Device DC Operating Conditions Notes (5), (6)									
Symbol	Parameter	Conditions	Min	Max	Unit					
VIH	High-level input voltage		2.0	V _{CC} + 0.3	V					
VIL	Low-level input voltage		-0.3	0.8	V					
V _{OH}	High-level TTL output voltage	I _{OH} = -4 mA DC (7)	2.4		V					
	High-level CMOS output voltage	I _{OH} = -0.6 mA DC (7)	3.84		V					
V _{OL}	Low-level output voltage	I _{OL} = 4 mA DC (7)		0.45	V					
I _I	I/O pin leakage current of dedicated input pins	$V_{I} = V_{CC}$ or ground	-10	10	μA					
I _{oz}	Tri-state output leakage current	$V_{O} = V_{CC}$ or ground	-10	10	μA					

Table 2	able 26. EP1810 Device Capacitance Notes (8)								
Symbol	Parameter	Conditions	Min	Max	Unit				
C _{IN}	Input pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		20	pF				
CIO	I/O pin capacitance	V _{OUT} = 0 V, f = 1.0 MHz		20	pF				
C _{CLK1}	C _{CLK1} pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		25	pF				
C _{CLK2}	C _{CLK2} pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		160	pF				

Table 27. EP1810 Device Icc Supply CurrentNotes (1), (5), (6)

Symbol	Parameter	Conditions	Speed Grade	Min	Тур	Max	Unit
I _{CC1}	V _{CC} supply current	$V_{I} = V_{CC}$ or ground, no load, -20			50	150	μA
	(non-Turbo, standby)	(9)	-35, -45		35	150	μA
I _{CC2}	V _{CC} supply current	$V_{I} = V_{CC}$ or ground, no load,	-20, -25		20	40	mA
	(non-Turbo, active)	f = 1.0 MHz <i>(9)</i>	-35, -45		10	30 (40)	mA
I _{CC3}	V _{CC} supply current (Turbo, active)	V _I = V _{CC} or ground, no load	-20, -25		180	225 (250)	mA
		f = 1.0 MHz <i>(9)</i>	-35, -45		100	180 (240)	mA

Notes to tables:

- (1) Numbers in parentheses are for industrial-temperature-range devices.
- (2) The minimum DC input is -0.3 V. During transitions, the inputs may undershoot to -2.0 V or overshoot to 7.0 V for input currents less than 100 mA and periods less than 20 ns.
- (3) Maximum V_{CC} rise time is 50 ms.
- (4) For EP1810 clocks: t_R and $t_F = 100$ ns (50 ns for industrial-temperature-range versions).
- (5) Typical values are for $T_A = 25^\circ \text{ C}$ and $V_{CC} = 5 \text{ V}$.
- (6) These values are specified in Table 24
- (7) The I_{OH} parameter refers to high-level TTL or CMOS output current; the I_{OL} parameter refers to low-level TTL output current.
- (8) The device capacitance is measured at 25° C and is sample-tested only.
- (9) Measured with a device programmed as four 12-bit counters.

Table 2	8. EP1810-20 & EP1810-25 Exte	rnal Timing Paramet	ers (Votes (1)			
Symbol	Parameter	Conditions	EP18	EP1810-20		10-25	Non-Turbo Adder	Unit
			Min	Max	Min	Max	(2)	1
t _{PD1}	Input to non-registered output	C1 = 35 pF		20.0		25.0	25.0	ns
t _{PD2}	I/O input to non-registered output	C1 = 35 pF		22.0		28.0	25.0	ns
t _{SU}	Global clock setup time		13.0		17.0		25.0	ns
t _H	Global clock hold time		0.0		0.0		0.0	ns
t _{CH}	Global clock high time		8.0		10.0		0.0	ns
t _{CL}	Global clock low time		8.0		10.0		0.0	ns
t _{co1}	Global clock to output delay	C1 = 35 pF		15.0		18.0	0.0	ns
t _{CNT}	Minimum global clock period	(3)		20.0		25.0	0.0	ns
f _{CNT}	Maximum internal frequency	(3)	50.0		40.0		0.0	MHz
t _{ASU}	Array clock setup time		8.0		10.0		25.0	ns
t _{AH}	Array clock hold time		8.0		10.0		0.0	ns
t _{ACO1}	Array clock to output delay	C1 = 35 pF		20.0		25.0	25.0	ns
t _{ODH}	Output data hold time after clock	C1 = 35 pF (4)	1.0		1.0		0.0	ns
t _{ACNT}	Array clock maximum clock period	(3)		20.0		25.0	0.0	ns
f _{acnt}	Maximum internal array clock frequency	(3)	50.0		40.0		0.0	ns
f _{MAX}	Maximum clock frequency	(5)	62.5		50.0		0.0	MHz

Table 29. EP1810-20 and EP1810-25 Internal Timing Parameters

Symbol	Parameter	Conditions	EP18	EP1810-20		10-25	Non-Turbo Adder	Unit
			Min	Max	Min	Max	(2)	1
t _{IN}	Input pad and buffer delay			5.0		7.0	0.0	ns
t _{IO}	I/O input pad and buffer delay			2.0		3.0	0.0	ns
t _{LAD}	Logic array delay			9.0		12.0	25.0	ns
t _{OD}	Output buffer and pad delay	C1 = 35 pF		6.0		6.0	0.0	ns
t _{ZX}	Output buffer enable delay	C1 = 35 pF		6.0		6.0	0.0	ns
t_{XZ}	Output buffer disable delay	C1 = 5 pF (6)		6.0		6.0	0.0	ns
t _{SU}	Register setup time		8.0		10.0		0.0	ns
t _H	Register hold time		5.0		10.0		0.0	ns
t _{IC}	Array clock delay			9.0		12.0	25.0	ns
t _{ICS}	Global clock delay			4.0		5.0	0.0	ns
t _{FD}	Feedback delay			3.0		3.0	-25.0	ns
t _{CLR}	Register clear time			9.0		12.0	25.0	ns

Table 3	0. EP1810-35 & EP1810-45 Exte	rnal Timing Paramet	ers N	lotes (1)			
Symbol	Parameter	Conditions	EP18	EP1810-35		10-45	Non-Turbo Adder	Unit
			Min	Max	Min	Max	(3)]
t _{PD1}	Input to non-registered output	C1 = 35 pF		35.0		45.0	30.0	ns
t _{PD2}	I/O input to non-registered output	C1 = 35 pF		40.0		50.0	30.0	ns
t _{su}	Global clock setup time		25.0		30.0		30.0	ns
t _H	Global clock hold time		0.0		0.0		0.0	ns
t _{сн}	Global clock high time		12.0		15.0		0.0	ns
t _{CL}	Global clock low time		12.0		15.0		0.0	ns
t _{co1}	Global clock to output delay	C1 = 35 pF		20.0		25.0	0.0	ns
t _{CNT}	Minimum global clock period	(3)		35.0		45.0	0.0	ns
f _{CNT}	Maximum internal frequency	(3)	28.6		22.2		0.0	MHz
t _{ASU}	Array clock setup time		10.0		11.0		30.0	ns
t _{AH}	Array clock hold time		15.0		18.0		0.0	ns
t _{ACO1}	Array clock to output delay	C1 = 35 pF		35.0		45.0	30.0	ns
t _{ODH}	Output data hold time after clock	C1 = 35 pF (4)	1.0		1.0			ns
t _{ACNT}	Array clock maximum clock period	(3)		35.0		45.0	0.0	ns
facnt	Maximum internal array clock frequency	(3)	28.6		22.2		0.0	ns
f _{MAX}	Maximum clock frequency	(5)	40		33.3		0.0	MHz

Table 31. EP1810-35 & EP1810-45 Internal Timing Parameters

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Symbol	Parameter	Conditions	EP18	EP1810-35		10-45	Non-Turbo Adder	Unit
			Min	Max	Min	Max	(2)	
t _{IN}	Input pad and buffer delay			7.0		6.0	0.0	ns
t _{IO}	I/O input pad and buffer delay			5.0		5.0	0.0	ns
t _{LAD}	Logic array delay			19.0		28.0	30.0	ns
t _{OD}	Output buffer and pad delay	C1 = 35 pF		9.0		11.0	0.0	ns
t_{ZX}	Output buffer enable delay	C1 = 35 pF		9.0		11.0	0.0	ns
t_{XZ}	Output buffer disable delay	C1 = 5 pF <i>(</i> 6)		9.0		11.0	0.0	ns
t _{SU}	Register setup time		10.0		10.0		0.0	ns
t _H	Register hold time		15.0		18.0		0.0	ns
t _{IC}	Array clock delay			19.0		28.0	30.0	ns
t _{ICS}	Global clock delay			4.0		8.0	0.0	ns
t _{FD}	Feedback delay			6.0		7.0	-30.0	ns
t _{CLR}	Register clear time			24.0		32.0	30.0	ns

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Notes to tables:

- (1) These values are specified in Table 24
- (2) The non-Turbo adder must be added to this parameter when the Turbo Bit option is off.
- (3) Measured with a device programmed as four 12-bit counters.
- (4) Sample-tested only. This parameter is a guideline based on extensive device characterization. This parameter applies for both global and array clocking.
- (5) The f_{MAX} values represent the highest frequency for pipelined data.
- (6) Sample-tested only for an output change of 500 mV.

Pin-Out Information

Table 32 provides pin-out information for EP1810 devices in 68-pin PGA packages.

Table 32. EP1810 PGA Pin-Outs

Pin	Function	Pin	Function	Pin	Function	Pin	Function
A2	I/O	B9	I/O	F10	GND	K4	INPUT
A3	I/O	B10	I/O	F11	I/O	K5	INPUT
A4	I/O	B11	I/O	G1	I/O	K6	VCC
A5	INPUT	C1	I/O	G2	I/O	K7	INPUT
A6	CLK4/INPUT	C2	I/O	G10	I/O	K8	INPUT
A7	CLK3/INPUT	C10	I/O	G11	I/O	K9	I/O
A8	INPUT	C11	I/O	H1	I/O	K10	I/O
A9	I/O	D1	I/O	H2	I/O	K11	I/O
A10	I/O	D2	I/O	H10	I/O	L2	I/O
B1	I/O	D10	I/O	H11	I/O	L3	I/O
B2	I/O	D11	I/O	J1	I/O	L4	INPUT
B3	I/O	E1	I/O	J2	I/O	L5	CLK1/INPUT
B4	INPUT	E2	I/O	J10	I/O	L6	CLK2/INPUT
B5	INPUT	E10	I/O	J11	I/O	L7	INPUT
B6	VCC	E11	I/O	K1	I/O	L8	I/O
B7	INPUT	F1	I/O	K2	I/O	L9	I/O
B8	INPUT	F2	GND	K3	I/O	L10	I/O



Rochester EPLD devices normally sold in the un-configured state are tested using the original manufacturer's test software to guarantee the data sheet specifications. In some cases, EPLD devices can be configured to the customer's design and fully tested as such.

EP600I Classic EPLD

Features

- Generally Intel's 5C060 device
- High-performance, 16-macrocell Classic EPLD
 - Combinatorial speeds with $t_{PD} = 45$ ns
 - Counter frequencies up to 22.2 MHz
 - Pipelined data rates up to 26.3 MHz
- Pin-, function-, and programming file-compatible with Altera's EP610 EPLDs
- Dependence of the second secon
- Macrocells individually programmable as D, T, JK, or SR flipflops, or for combinatorial operation
- Available in windowed ceramic and one-time-programmable plastic packages:
 - 24-pin dual in-line packages (CerDIP and PDIP)
 - 28-pin plastic J-lead chip carrier (PLCC)

EP600I Classic EPLD

Data Sheet Supplement

Absolute Maximum Ratings See Operating Requirements for Altera Devices in the current Altera Data Book.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{cc}	Supply voltage	Note (1)	-2.0	7.0	v
V ₁	DC input voltage	Notes (1), (2)	-0.5	V _{CC} + 0.5	V
T _{STG}	Storage temperature		-65	150	°C
T _{AMB}	Ambient temperature	Note (3)	-10	85	°C

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	Supply voltage		4.75	5.25	v
V ₁	Input voltage		0	V _{cc}	v
vo	Output voltage		0	Vcc	V
TA	Operating temperature	For commercial use	0	70	°C
T _A	Operating temperature	For industrial use	-40	85	°C
т _с	Case temperature	For military use	-55	125	°C
t _R	Input rise time	Note (4)		500	ns
t _F	Input fall time	Note (4)		500	ns

DC Operating Conditions Note (5)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V _{IH}	High-level input voltage	Note (6)	2.0	1	V _{CC} + 0.3	V	
VIL	Low-level input voltage	Note (6)	-0.3		0.8	v	
V _{он}	High-level output voltage	$I_{OH} = -4 \text{ mA DC}, V_{CC} = \text{min}$	2.4			V	
VOL	Low-level output voltage	I _{OL} = 4 mA DC, V _{CC} = min			0.45	V	
I _I	Input leakage current	V _{CC} = max, GND < V _{IN} < V _{CC}	-10	1	10	μA	
loz	Tri-state output off-state current	V _{CC} = max, GND < V _{OUT} < V _{CC}	-10		10	μA	
I _{CC1}	V _{CC} supply current (non-turbo, standby)	$V_{CC} = max, V_{IN} = V_{CC} \text{ or GND},$ Note (7)		50	100	μA	
I _{CC2}	V _{CC} supply current (non-turbo, active)	$V_{CC} = max, V_{IN} = V_{CC} \text{ or GND},$ no load, f _{IN} = 1 MHz, <i>Note (8)</i>		10	15	mA	

Capacitance Note (5)

Symbol	Parameter Conditions		Min	Max	Unit
CIN	Input capacitance	V _{IN} = 0 V, f = 1.0 MHz		20	pF
COUT	Output capacitance	V _{OUT} = 0 V, f = 1.0 MHz		20	pF
C _{CLK1}	CLK1 pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		20	pF
C _{CLK2}	CLK2 pin capacitance	V _{IN} = 0 V, f = 1.0 MHz		50	pF

Data Sheet Supplement

EP600I Classic EPLD

AC Operating Conditions Note (5)

External Timing Parameters			EP600I-45		EP600I-55		Non-Turbo Adder	
Symbol	Parameter	Conditions	Min	Max	Min	Max	Note (9)	Unit
t _{PD1}	Input to non-registered output			43	-	53	25	ns
t _{PD2}	I/O input to non-registered output			45		55	25	ns
t _{PZX}	Input to output enable	Note (10)		45		55	25	ns
t _{PXZ}	Input to output disable	Note (10)		45		55	25	ns
tCLR	Asynchronous output clear time			45		55	25	ns

Global Clock Mode		EP600I-45		EP600I-55		Non-Turbo Adder		
Symbol	Parameter	Conditions	Min	Max	Min	Max	Note (9)	Unit
f _{MAX}	Maximum frequency		26.3		23.3		0	MHz
t _{SU1}	Input setup time		36		41		25	ns
t _{SU2}	I/O setup time		38		43		25	ns
t _H	Input hold time		0		0		0	ns
t _{сн}	Clock high time		17.5		21.5		0	ns
t _{CL}	Clock low time		17.5		21.5		0	ns
t _{co}	Clock to output delay			22		25	0	ns
tCNT	Minimum clock period			45		55	25	ns
f _{CNT}	Internal maximum frequency		22.2		18.2		0	MHz

Array Clock Mode		EP6001-45		EP6001-55		Non-Turbo Adder		
Symbol	Parameter	Conditions	Min	Max	Min	Max	Note (9)	Unit
f _{MAX}	Maximum frequency		28.6		23.3		0	MHz
t _{ASU1}	Input setup time		10		10		25	ns
tASU2	I/O setup time		12		12		25	ns
tAH	Input hold time		15		15		0	ns
tACH	Clock high time		17.5		21.5		25	ns
tACL	Clock low time		17.5		21.5		25	ns
tACO	Clock to output delay			50		58	25	ns
TACNT	Minimum clock period			45		55	25	ns
f ACNT	Internal maximum frequency		22.2		18.2		0	MHz

Notes to tables:

- (1) Voltage is with respect to GND.
- The minimum DC input is -0.5 V. During transitions, the inputs may undershoot (2) to -2.0 V or overshoot to +7.0 V for periods less than 20 ns under no-load conditions.
- This parameter is under bias. Extended temperature versions are also available. (3)
- For all Clocks: t_R and $t_F = 250$ ns (maximum). (4)
- Operating conditions: $T_A = 0^\circ C$ to $70^\circ C$, $V_{CC} = 5.0 V \pm 5\%$ for commercial use. $T_A = -40^\circ C$ to $85^\circ C$, $V_{CC} = 5.0 V \pm 10\%$ for industrial use. $T_C = -55^\circ C$ to $125^\circ C$, $V_{CC} = 5.0 V \pm 10\%$ for military use. (5)
- Absolute values with respect to device GND; all over- and undershoots due to (6) system or tester noise are included.
- When the Turbo Bit is not set (non-turbo mode), device enters standby mode (7) approximately 100 ns after the last input transition.
- Measured with a device programmed as a 16-bit counter. (8)
- When the Turbo Bit is not set (non-turbo mode), the non-turbo adder values must (9) be added to the appropriate AC parameter to determine worst-case timing.
- (10) The t_{PXX} and t_{PXZ} parameters are measured at ±0.5 V from steady state voltage as driven by the output load specification; t_{PZX} is measured with $C_L = 5 \text{ pF}$.

Rochester Electronics guarantees performance of its semiconductor products to the original OEM specifications. "Typical" values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing. Rochester Electronics reserves the right to make changes without further notice to any specification herein.